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74HC2G04; 74HCT2G04

Dual inverter

Rev. 01 — 15 November 2006

Product data sheet

1. General description

The 74HC2G04; 74HCT2G04 is a high-speed Si-gate CMOS device.

The 74HC2G04; 74HCT2G04 provides two inverting buffers.

2. Features

- Wide supply voltage range from 2.0 V to 6.0 V
- Complies with JEDEC standard no. 7A
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114-D exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Low power dissipation
- Balanced propagation delays
- Unlimited input rise and fall times
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

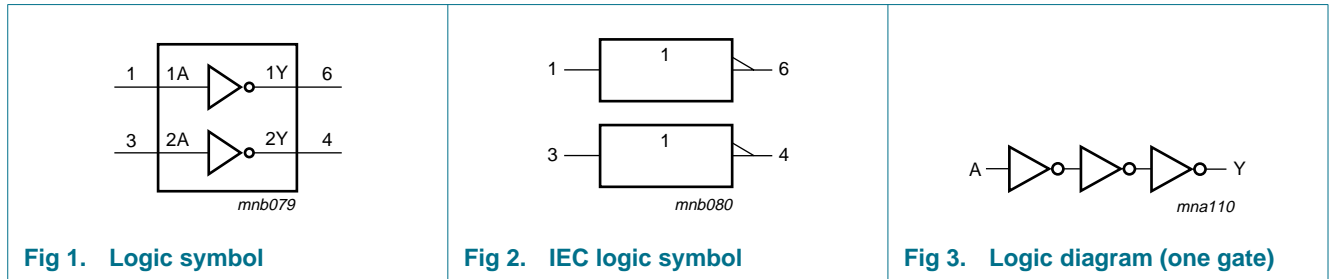
Type number	Package			
	Temperature range	Name	Description	Version
74HC2G04GW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SC-88	plastic surface-mounted package; 6 leads	SOT363
74HC2G04GV	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457
74HCT2G04GW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SC-88	plastic surface-mounted package; 6 leads	SOT363
74HCT2G04GV	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457

4. Marking

Table 2. Marking

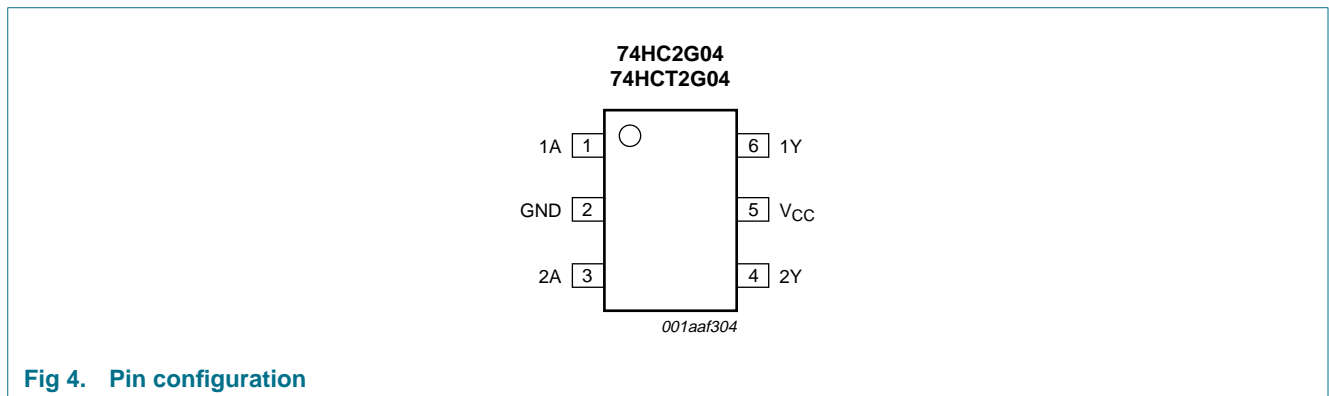
Type number	Marking code
74HC2G04GW	H4
74HC2G04GV	H04
74HCT2G04GW	T4
74HCT2G04GV	T04

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V _{CC}	5	supply voltage
1Y	6	data output

7. Functional description

Table 4. Function table^[1]

Input	Output
nA	nY
L	H
H	L

[1] H = HIGH voltage level;
L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	[1] -	±20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	[1] -	±20	mA
I_O	output current	$V_O = -0.5\text{ V}$ to $V_{CC} + 0.5\text{ V}$	[1] -	±25	mA
I_{CC}	supply current		[1] -	+50	mA
I_{GND}	ground current		[1] -	-50	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation		[2] -	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 and SC-74 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Type 74HC2G04						
V_{CC}	supply voltage		2.0	5.0	6.0	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	°C
t_r	rise time	except for Schmitt trigger inputs				
		$V_{CC} = 2.0\text{ V}$	-	-	1000	ns
		$V_{CC} = 4.5\text{ V}$	-	-	500	ns
		$V_{CC} = 6.0\text{ V}$	-	-	400	ns
t_f	fall time	except for Schmitt trigger inputs				
		$V_{CC} = 2.0\text{ V}$	-	-	1000	ns
		$V_{CC} = 4.5\text{ V}$	-	-	500	ns
		$V_{CC} = 6.0\text{ V}$	-	-	400	ns

Table 6. Recommended operating conditions ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Type 74HCT2G04						
V_{CC}	supply voltage		4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	°C
t_r	rise time	except for Schmitt trigger inputs				
		$V_{CC} = 4.5\text{ V}$	-	-	500	ns
t_f	fall time	except for Schmitt trigger inputs				
		$V_{CC} = 4.5\text{ V}$	-	-	500	ns

10. Static characteristics

Table 7. Static characteristics for 74HC2G04

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = 25\text{ °C}$						
V_{IH}	HIGH-level input voltage	$V_{CC} = 2.0\text{ V}$	1.5	1.2	-	V
		$V_{CC} = 4.5\text{ V}$	3.15	2.4	-	V
		$V_{CC} = 6.0\text{ V}$	4.2	3.2	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 2.0\text{ V}$	-	0.8	0.5	V
		$V_{CC} = 4.5\text{ V}$	-	2.1	1.35	V
		$V_{CC} = 6.0\text{ V}$	-	2.8	1.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20\text{ }\mu\text{A}$; $V_{CC} = 2.0\text{ V}$	1.9	2.0	-	V
		$I_O = -20\text{ }\mu\text{A}$; $V_{CC} = 4.5\text{ V}$	4.4	4.5	-	V
		$I_O = -20\text{ }\mu\text{A}$; $V_{CC} = 6.0\text{ V}$	5.9	6.0	-	V
		$I_O = -4.0\text{ mA}$; $V_{CC} = 4.5\text{ V}$	4.18	4.32	-	V
		$I_O = -5.2\text{ mA}$; $V_{CC} = 6.0\text{ V}$	5.68	5.81	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 2.0\text{ V}$	-	0	0.1	V
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 4.5\text{ V}$	-	0	0.1	V
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 6.0\text{ V}$	-	0	0.1	V
		$I_O = 4.0\text{ mA}$; $V_{CC} = 4.5\text{ V}$	-	0.15	0.26	V
		$I_O = 5.2\text{ mA}$; $V_{CC} = 6.0\text{ V}$	-	0.16	0.26	V
I_I	input leakage current	$V_I = \text{GND}$ or V_{CC} ; $V_{CC} = 6.0\text{ V}$	-	-	± 0.1	μA
I_{CC}	supply current	$V_I = \text{GND}$ or V_{CC} ; $I_O = 0\text{ A}$; $V_{CC} = 6.0\text{ V}$	-	-	1.0	μA
C_I	input capacitance		-	1.5	-	pF

Table 7. Static characteristics for 74HC2G04 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	-	-	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	-	-	V
		I _O = -4.0 mA; V _{CC} = 4.5 V	4.13	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 2.0 V	-	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	-	0.33	V
I _I	input leakage current	V _I = GND or V _{CC} ; V _{CC} = 6.0 V	-	-	±1.0	μA
		V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 6.0 V	-	-	10.0	μA
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	-	-	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	-	-	V
		I _O = -4.0 mA; V _{CC} = 4.5 V	3.7	-	-	V
I _O	I _O = -5.2 mA; V _{CC} = 6.0 V	5.2	-	-	V	

Table 7. Static characteristics for 74HC2G04 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 2.0 V	-	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	-	0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	-	0.4	V
I _I	input leakage current	V _I = GND or V _{CC} ; V _{CC} = 6.0 V	-	-	±1.0	μA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 6.0 V	-	-	20.0	μA

Table 8. Static characteristics for 74HCT2G04

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	4.5	-	V
		I _O = -4.0 mA; V _{CC} = 4.5 V	4.18	4.32	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	V
I _I	input leakage current	V _I = GND or V _{CC} ; V _{CC} = 5.5 V	-	-	±0.1	μA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.0	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 2.1 V; V _{CC} = 4.5 V to 5.5 V; I _O = 0 A	-	-	300	μA
C _I	input capacitance		-	1.5	-	pF
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -4.0 mA; V _{CC} = 4.5 V	4.13	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	-	0.33	V
I _I	input leakage current	V _I = GND or V _{CC} ; V _{CC} = 5.5 V	-	-	±1.0	μA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 5.5 V	-	-	10.0	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 2.1 V; V _{CC} = 4.5 V to 5.5 V; I _O = 0 A	-	-	375	μA

Table 8. Static characteristics for 74HCT2G04 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -4.0 mA; V _{CC} = 4.5 V	3.7	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	-	0.4	V
I _I	input leakage current	V _I = GND or V _{CC} ; V _{CC} = 5.5 V	-	-	±1.0	μA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 5.5 V	-	-	20.0	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 2.1 V; V _{CC} = 4.5 V to 5.5 V; I _O = 0 A	-	-	410	μA

11. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 6](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
74HC2G04									
t _{pd}	propagation delay	nA to nY; see Figure 5 [1]							
		V _{CC} = 2.0 V; C _L = 50 pF	-	22	75	-	90	110	ns
		V _{CC} = 4.5 V; C _L = 50 pF	-	8	15	-	18	22	ns
		V _{CC} = 6.0 V; C _L = 50 pF	-	6	13	-	16	20	ns
t _t	transition time	nY; see Figure 5 [2]							
		V _{CC} = 2.0 V; C _L = 50 pF	-	18	75	-	95	125	ns
		V _{CC} = 4.5 V; C _L = 50 pF	-	6	15	-	19	25	ns
		V _{CC} = 6.0 V; C _L = 50 pF	-	5	13	-	16	20	ns
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC} [3]	-	9	-	-	-	-	pF

Table 9. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 6](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
74HCT2G04									
t _{pd}	propagation delay	nA to nY; see Figure 5 [1]							
		V _{CC} = 4.5 V; C _L = 50 pF	-	10	18	-	23	29	ns
t _t	transition time	nY; see Figure 5 [2]							
		V _{CC} = 4.5 V; C _L = 50 pF	-	6	15	-	19	22	ns
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC} - 1.5 V [3]	-	9	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [2] t_t is the same as t_{TLH} and t_{THL}.
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

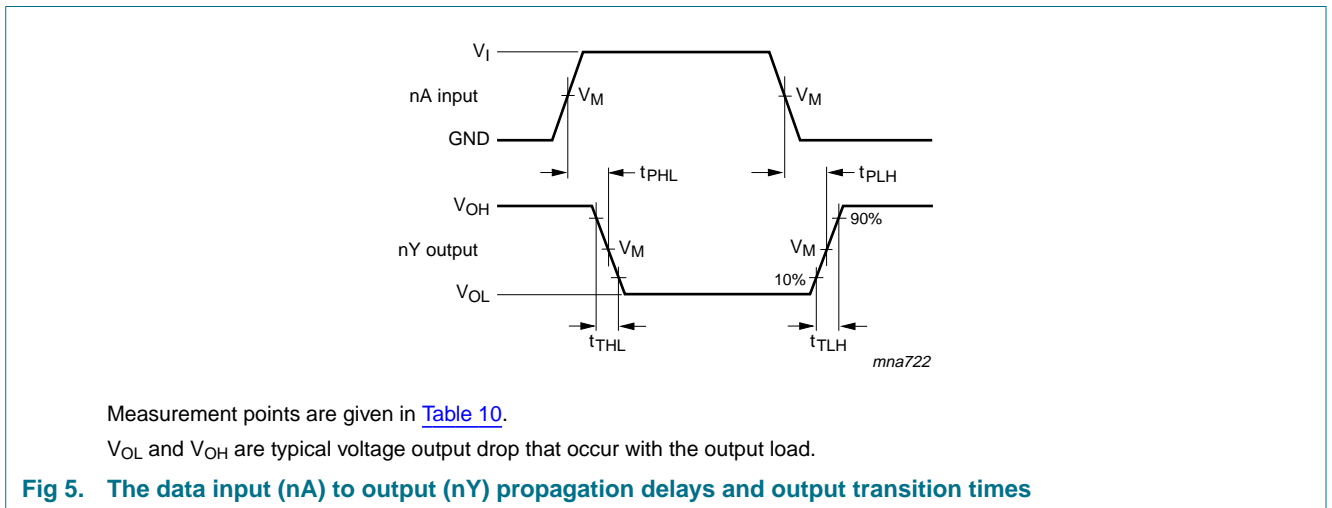
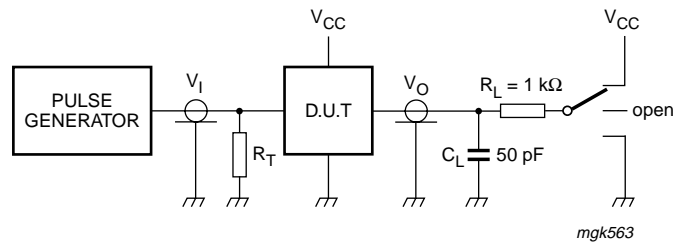


Table 10. Measurement points

Type	Input			Output
	V _M	V _I	t _r = t _f	V _M
74HC2G04	0.5V _{CC}	GND to V _{CC}	6.0 ns	0.5V _{CC}
74HCT2G04	1.3 V	GND to 3.0 V	6.0 ns	1.3 V



Test data is given in [Table 11](#).

Definitions test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

Fig 6. Load circuitry for switching times

Table 11. Test data

Type	Input		Test
	V_I	t_r, t_f	t_{PHL}, t_{PLH}
74HC2G04	GND to V_{CC}	6 ns	open
74HCT2G04	GND to 3.0 V	6 ns	open

13. Package outline

Plastic surface-mounted package; 6 leads

SOT363

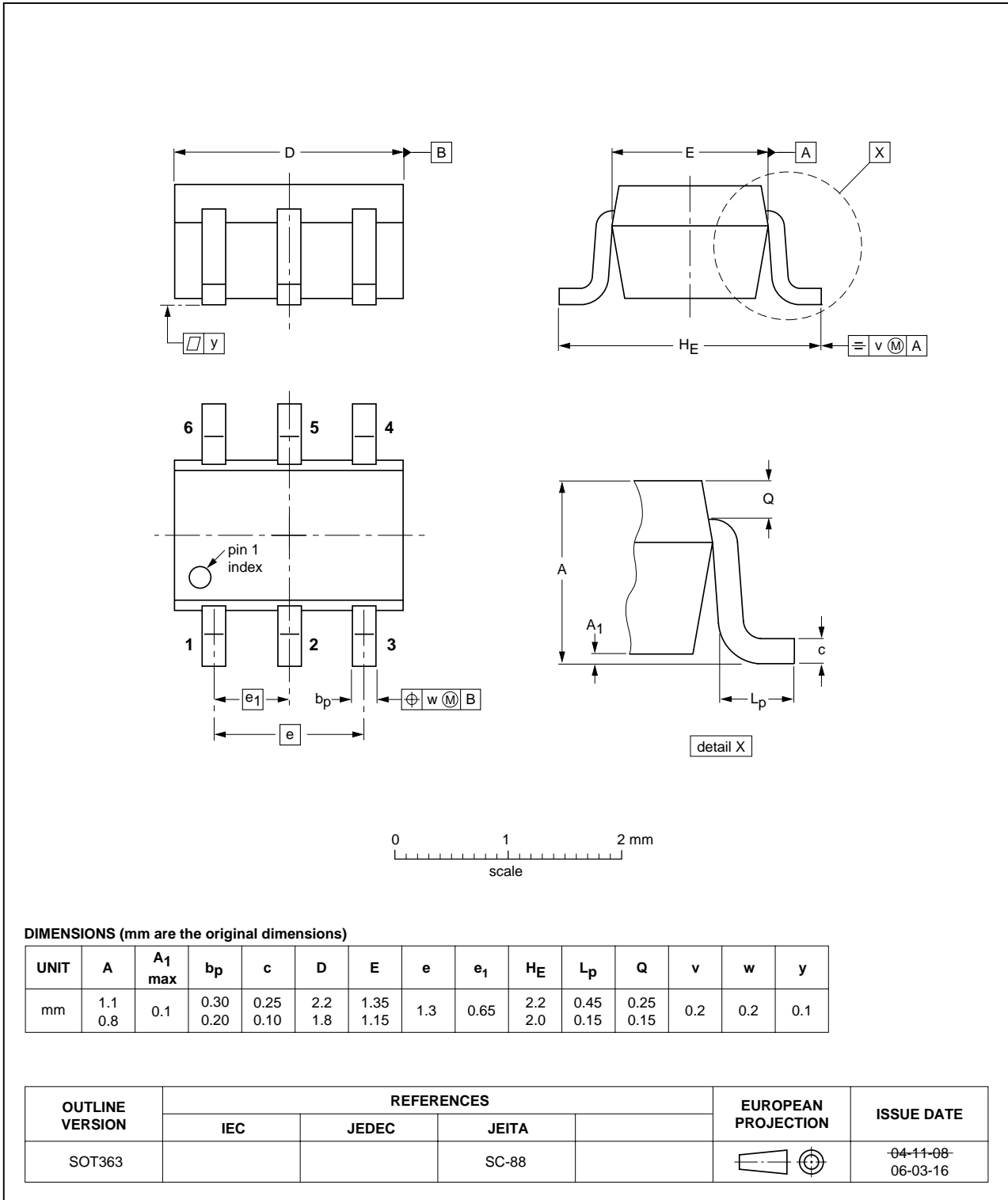


Fig 7. Package outline SOT363 (SC-88)

Plastic surface-mounted package (TSOP6); 6 leads

SOT457

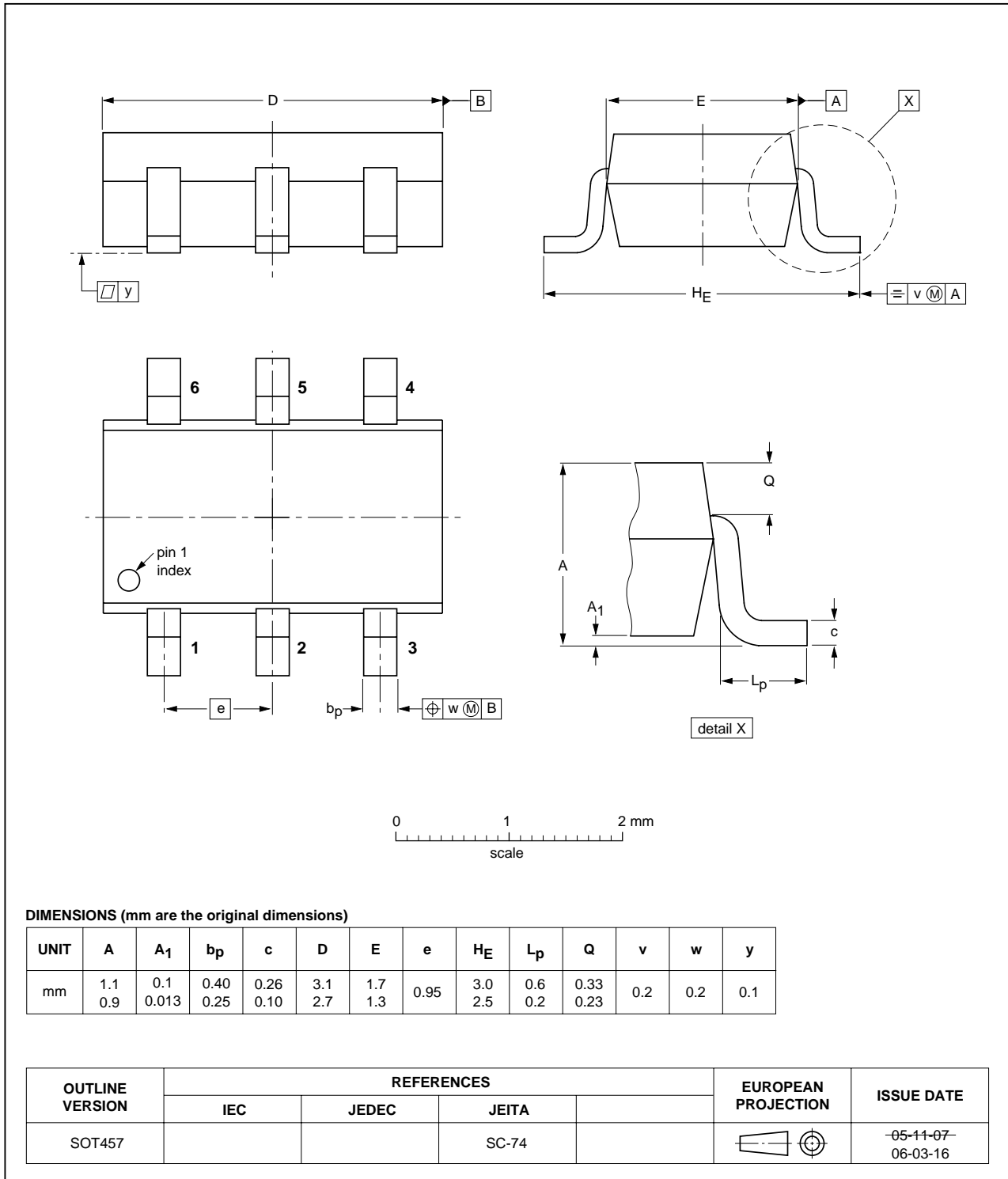


Fig 8. Package outline SOT457 (SC-74)

14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
DUT	Device Under Test

15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G04_1	20061115	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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